

μPD166108GR

MOS INTEGRATED CIRCUIT

R07DS1119EJ0100 Rev.1.00 Sep 20, 2013

Description

The µPD166108 is an N-channel low side driver with embedded protection function.

When device is overtemperature or overcurrent is generated in output MOS, the protection function operates to prevent destruction and degradation of the product, and also outputs self-diagnostic signal.

Features

- High temperature operation (Tch = 175° C MAX.)
- Low on-state resistance

 $R_{DS(ON)} = 200 \text{ m}\Omega \text{ MAX.} (V_{IN} = 5.0 \text{V}, I_O = 0.9 \text{A}, \text{Tch} = 25^{\circ}\text{C})$

- Built-in protection circuit
 - Current limitation
 - Overtemperature protection
- Built in dynamic clamp circuit
- Dual channel Low-side switch
- Package: Power SOP 8

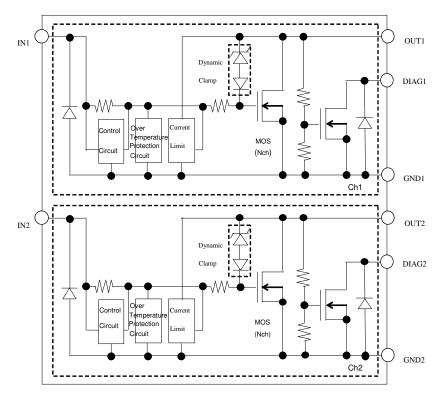
Application

• Switching of all types of 14 V DC grounded loads, such as inductor, resistor and capacitor

Ordering Information

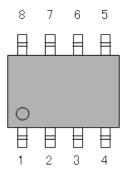
Part No.	Lead Plating	Packing	Package
μPD166108GR-E1-AY	Sn	Tape 2500 p/reel	Power SOP 8
μPD166108GR-E2-AY	Sn	Tape 2500 p/reel	Power SOP 8

Block Diagram



Pin Configuration

• Power SOP 8



Pin Functions

Pin No.	Pin Name	Function		
1	IN1	Input pin1 (active level is high)		
2	DIAG1	DIAG pin1		
3	IN2	Input pin2 (active level is high)		
4	DIAG2	DIAG pin2		
5	GND2	Ground pin2		
6	OUT2	Output pin2		
7	GND1	Ground pin1		
8	OUT1	Output pin1		

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C, unless otherwise specified)$

Item	Symbol	Rating	Unit	Condition
Output voltage	VOUT	40	V/ch	VIN=0V, DC susceptibility (without Flyback voltage)
Input voltage	VIN	-1.0 to 7.0	V/ch	
Negative input current	IIL	-10	mA/ch	
DIAG output voltage	Vdiag	-0.3 to 7.0	V/ch	
DIAG output current	Idiag	1.0	mA/ch	
Output current	IOUT(DC)	1.6	A/ch	VIN=5V
Total power dissipation	PD	2.3	W	2ch turn ON at the same moment *1
Channel temperature	Tch	175	°C	
Storage temperature	Tstg	-55 to 175	°C	
Dynamic clamp susceptibility (single pules)	EAS	100	mJ/ch	VBAT=16V, L=50mH, VIN=5V→0V
		30	mJ/ch	VBAT=16V, L=200mH, VIN=5V→0V, Tch=150°C
Dynamic clamp susceptibility (repetitive pules)	Ecl	40	mJ/ch	VBAT=16V, L=110mH, f=20Hz Duty=50%, VIN=5V→0V

Note: When mounted on a epoxy PCB (where FR-4 is 10 cm \times 10 cm, dimension of copper foil is 15% and thickness of copper foil is 35 μ m), PW = 10 s

Electrical Characteristics

(Tch = 25° C, unless otherwise specified)

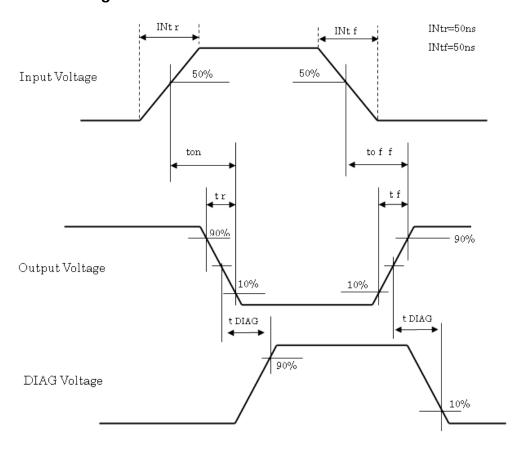
Item	Symbol	MIN.	TYP.	MAX.	Unit	Condition	
Output clamping voltage	VOUT	40		60	V	lo=1mA, VIN=0V	
		10		100	μ A /ch		Ta = 25°C
Output Off leakage	IOUT	10		200	μA/ch	VIN=0V, VOUT=18V	Ta = -40 to 125°C
current		25		300	μ A /ch		Ta = 125 to 175°C
		10		100	μA/ch	IIN=-5mA, VOUT=18V	
High Level Input	IIH			400	μA		Ta = 25°C
current				500	μA	VIN=5V, VOUT=0V	Ta = -40 to 175°C
Low Level Input current	IIL	-10		10	μA	VIN=0V, VOUT=18V	Ta = -40 to 175°C
High Level Input		3.0			V	Io=0.9A, VOUT=0.5V	Ta = -40 to 125°C
voltage	VIH	3.0			V	Io=0.9A, VOUT=1.0V	Ta = 125 to 175°C
Low Level Input voltage	VIL			1.5	V	VOUT=10V, lo=10mA	Ta = -40 to 175°C
Negative input voltage	VNI	-1.0		0	V	IIN = -5mA, VOUT = 18V	•
DIAG L-level output		1		3	V	VIN=0V, RDIAG=10kΩ	Ta = -40 to 125°C
voltage	Voutdiag	0.8		3	V	Vcc=5V	Ta = 125 to 175°C
		Vcc-0.5			V/ch	VIN=0V, VOUT=0V	Ta = -40 to 125°C
DIAO I I II	VdiagH	Vcc-0.8			V/ch	RDIAG=10kΩ, Vcc=5V	Ta = 125 to 175°C
DIAG output voltage	VdiagL			0.5	V/ch	VIN=0V, VOUT=4.5V RDIAG=10kΩ, Vcc=5V	Ta = -40 to 175°C
DIAG leak current	IDiagleak			50	μ A /ch	VIN = 0V, Vcc = 5V	Ta = -40 to 125°C
				75	μ A /ch		Ta = 125 to 175°C
	Rout(on)			200	mΩ/ch	VIN = 5.0V, lo = 0.9A	Ta = 25°C
				360	mΩ/ch		Ta = -40 to 125°C
				400	mΩ/ch		Ta = 125 to 175°C
ON-state resistance				240	mΩ/ch	VIN = 3.0V, lo = 0.9A	Ta = 25°C
				435	mΩ/ch		Ta = -40 to 125°C
				490	mΩ/ch		Ta = 125 to 175°C
Turn-on time	ton			80	μs	V 40V D 000	
Rise time	tr			60	μs	$V_{BAT}=18V, R_L=22\Omega,$	
Turn-off time	toff			80	μs	VIN = 0V to 5V, RIN = 10Ω, RDIAG=10ks	1
Fall time	tf			60	μs		.2
Turn-on time	ton *1			80	μs	V 10V D 000	
Rise time	tr *1			60	μs	$V_{BAT} = 18V, R_L = 22\Omega,$	
Turn-off time	toff *1			100	μS	VIN = OPEN to 5V, RIN = 10Ω, RDIAG = $10kΩ$	
Fall time	tf *1			60	μs		
DIAG response time	tDIAG			50	μs		
Thermal shutdown detection temperature *2	THI	175			°C	VIN = 5V	
		1		20	Α	\/\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Ta = -40 to 125°C
		1		10	Α	VIN=3 to 7V, $R_L=0\Omega$	Ta = 125 to 175°C
Current limit *3	Is	1.6		20	A		Ta = -40 to 125°C
		1.6		10	A	VIN=5V,R _L =0 Ω	Ta = 125 to 175°C
Input frequency	fIN			1	kHz	VIN=5V,Duty=50%,variat	

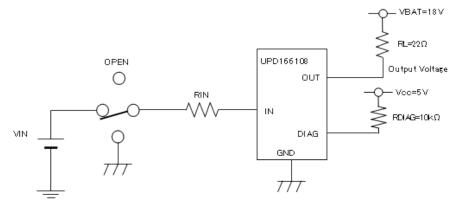
Notes: 1. Not subject to production test, specified by design.

^{2.} Thermal shutdown returns by oneself.

^{3.} The device does not destroy under Vbat =16V and short circuit condition. (within 24H continuously)

Definition of Switching Time





Switching Measurement Circuit

Truth Table

Item	V _{IN}	V _{OUT}	V_{DIAG}
Normal operation	L	Н	L
	Н	L	Н
Overtemperature detection	L	Н	L
	Н	Н	L
Overcurrent detection	L	Н	L
	Н	*	*
Disconnection detection	L	L	Н

^{*}: Output control condition

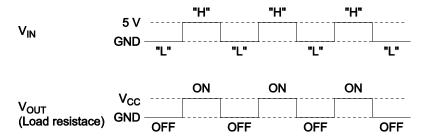
Outline of Functions

Pre-Driver (Charge Pump Circuit) ON/OFF Control

When the input voltage of the input pin (IN) is high level (3.0 V or more), the output MOS (Nch) turns on.

When the output voltage of the input pin (IN) is low level (1.5 V or less), the output MOS (Nch) turns off.

Charge pump circuit is built-in to drive the output MOS (Nch) that is connected to the high side.

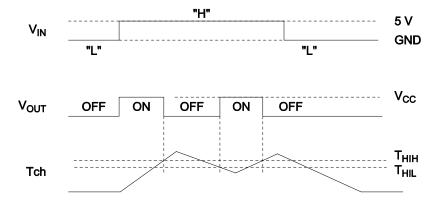


Overcurrent Detection Circuit

This circuit detects overcurrent to output pin (OUT) caused by short circuit etc., and feeds back detection signal to control circuit. When the overcurrent is detected, the current limitation circuit and the control circuit start operation. The output current is restricted in order to prevent destruction and degradation of the product.

Overtemperature Detection Circuit

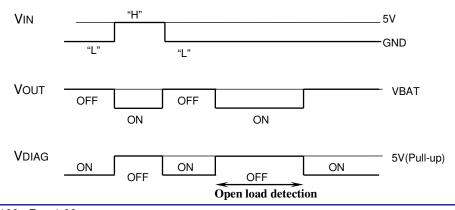
This circuit detects overtemperature by output MOS (Nch) driving, and feeds back detection signal to control circuit. When the circuit detects overtemperature, the protection function of the control circuit operates and output is shutdown. Output MOS (Nch) automatically restarts when channel temperature cools down after shutdown.



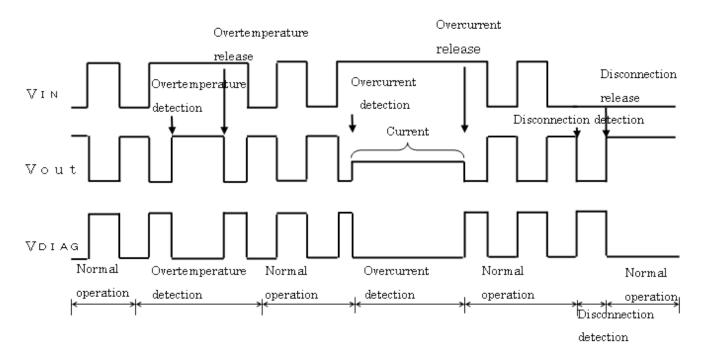
Open Load Detection Circuit

This circuit detects Open Load of output terminal. However, In case of using Open Load detection function, it is necessary to connect pull-up resistor (10Kohm±10%) with output terminal. (There are no electric characteristics influences in other circuit by presence of pull-up resistor.)

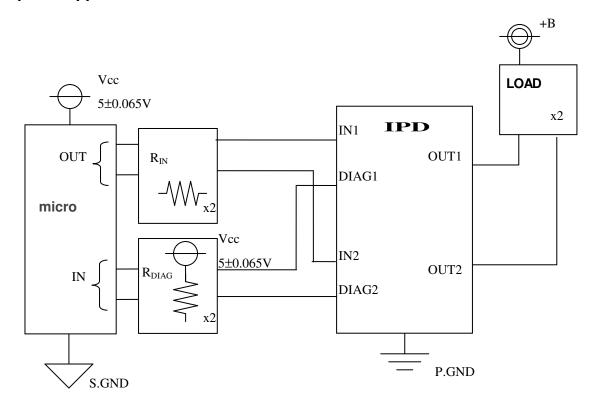
Open Load is detected by inputting low-level (1.5V or less) to input terminal (IN). DAIG terminal outputs Hi-Z (pull-up: high-level) when the output terminal is open.



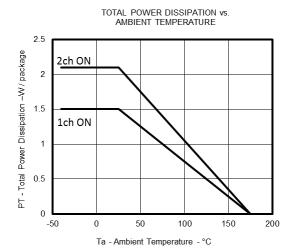
Timing Chart

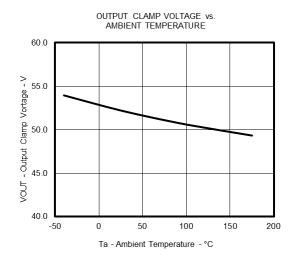


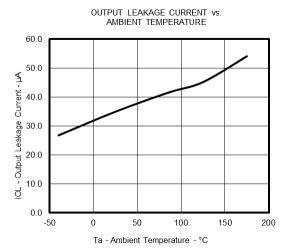
Example of Application Circuit

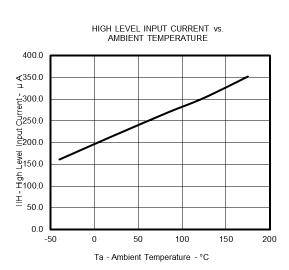


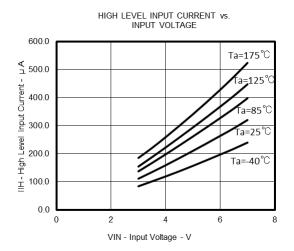
Typical Characteristics

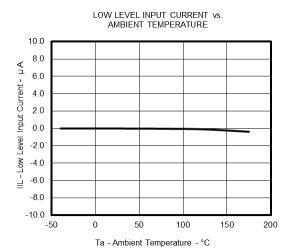


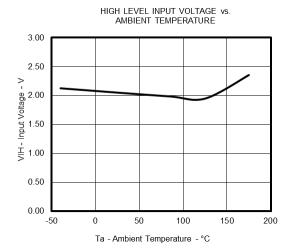


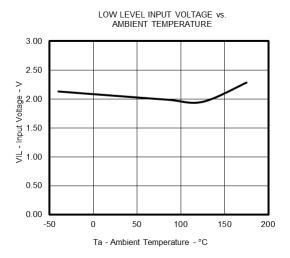


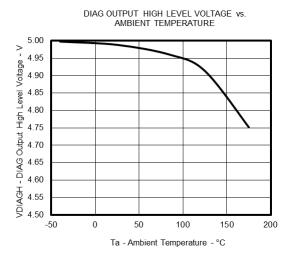


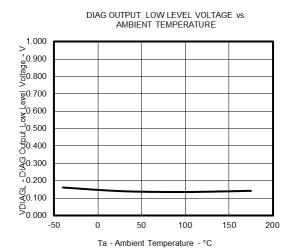


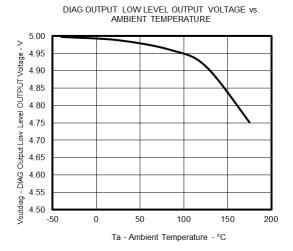


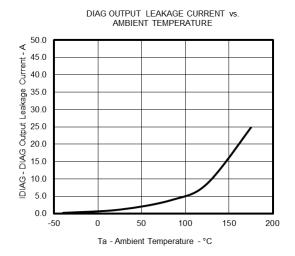


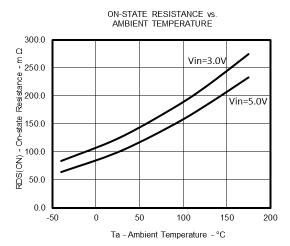


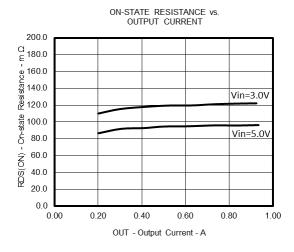


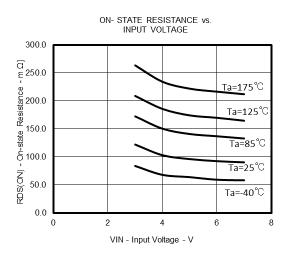


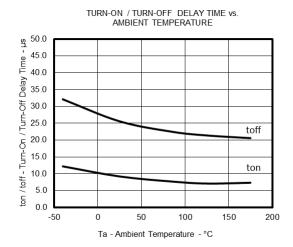


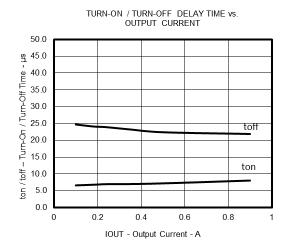


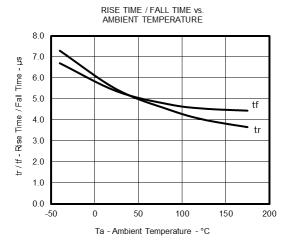


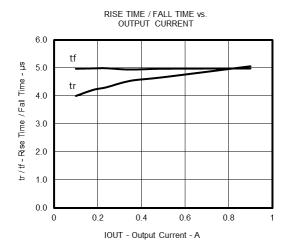


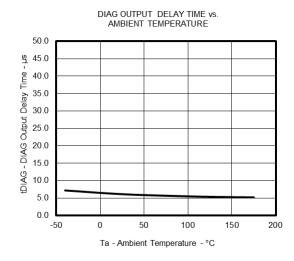


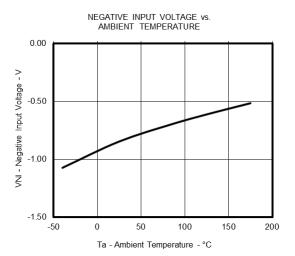


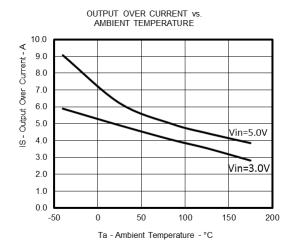




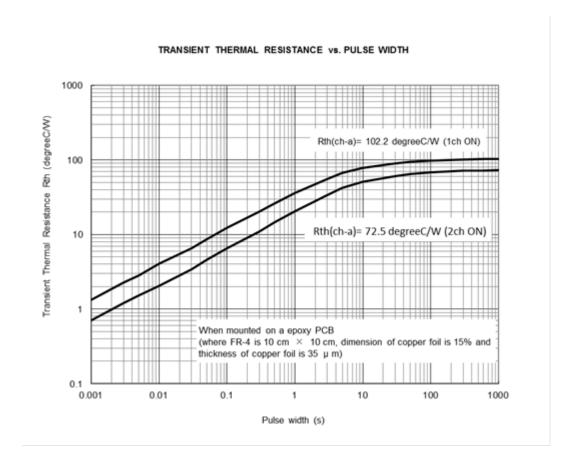




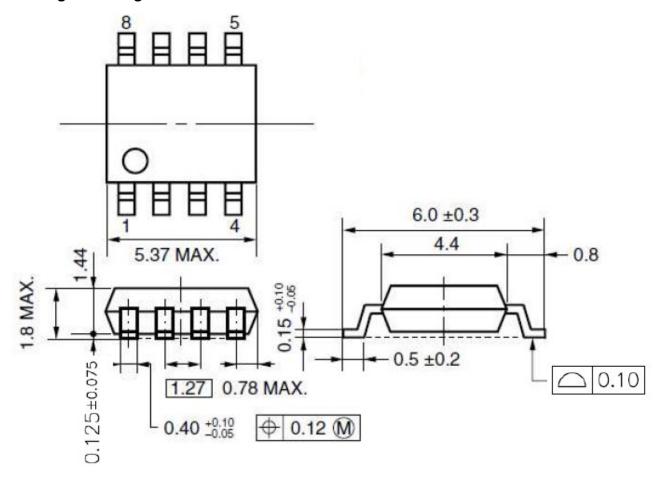




Transient Thermal Resistance Characteristics

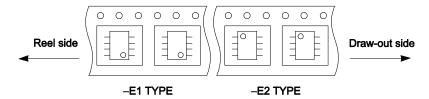


Package Drawing



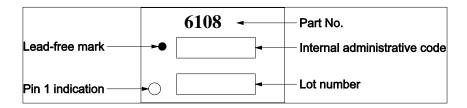
Taping Information

There are two types (-E1, -E2) of taping depending on the direction of the device.



Marking Information

This figure indicates the marking items and arrangement. However, details of the letterform, the size and the position aren't indicated.



Recommended Soldering Conditions

The µPD166015 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact a Renesas Electronics sales representative.

For technical information, see the following website.

Semiconductor Package Mount Manual (http://www.renesas.com/prod/package/manual/)

- µPD166108GR-E1-AY Note: Power SOP 8
- μPD166108GR-E2-AY Note: Power SOP 8

Process	Conditions	Symbol
Infrared reflow	Maximum temperature (package's surface temperature): 260°C or below,	IR60-00-3
	Time at maximum temperature: 10 seconds or less,	
	Time at temperature higher than 220°C: 60 seconds or less,	
	Preheating time at 160°C to 180°C: 60 to 120 seconds, Times: Three times,	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	
Partial Heating	Pin temperature: 300°C or below,	_
Method	Heat time: 3 seconds or less (Per each side of the device),	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	

Note: Pb-free (This product does not contain Pb in the external electrode.)

Revision History

$\mu PD166108GR \ Data \ Sheet$

		Description		
Rev.	Date	Page Summary		
1.00	Sep 20, 2013	_	First Edition Issued	

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